**Preliminary** 

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6L55E

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

• Two devices are built into the super-thin and ultra-super-mini (6-pin) ES6 package.

#### **Mounted Devices**

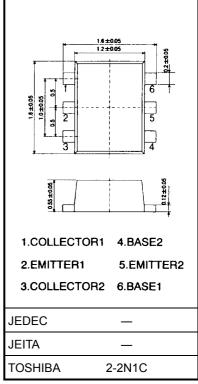
	Q1: SSM (TESM)	Q2: TESM
Three-pin (SSM/TESM) product No.	MT3S07S (MT3S07T)	MT3S005T

#### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1	Q2	Unit		
Collector-base voltage	$V_{CBO}$	10	10	V		
Collector-emitter voltage	V <sub>CEO</sub>	5	5	V		
Emitter-base voltage	V <sub>EBO</sub>	1.5	2	V		
Collector current	IC	25	40	mA		
Base current	ΙΒ	10 10		10 10		mA
Collector power dissipation	P <sub>C</sub> (Note 1)	150		mW		
Junction temperature	Tj	125		125		°C
Storage temperature range	T <sub>stg</sub>	-55~125		°C		

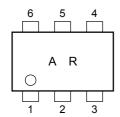
Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board

# Unit: mm

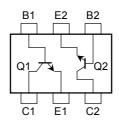


#### Weight: 3 mg (typ.)

### Marking



#### **Pin Connections**



# **Electrical Characteristics Q1-Side (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V, } I_C = 0$	_	_	1	μА
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	70	_	140	_
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	10	12	_	GHz
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	6.5	_	dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}, f = 2 \text{ GHz}$	4	7	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.6	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.5	3	ub
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.45	0.85	pF

# **Electrical Characteristics Q2-Side (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μΑ
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA}$	80	_	140	_
Transition frequency	f <sub>T</sub>	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA}$	2	4.5	_	GHz
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	7.5	_	dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 1 \text{ GHz}$	7.5	10.5	_	ub
Noise figure	NF	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	1.4	2.2	dB
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.95	1.15	pF

Note 2:  $C_{\text{re}}$  is measured by 3 terminal method with capacitance bridge.

#### **Handling Precaution**

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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